

# onsemi MC74VHC1G08 Single 2 Input And Gate User Guide

Home » onsemi » onsemi MC74VHC1G08 Single 2 Input And Gate User Guide 🖫

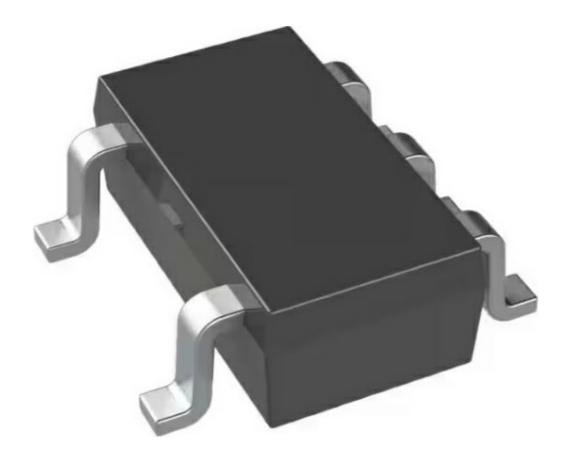


#### **Contents**

- 1 onsemi MC74VHC1G08 Single 2 Input And
- 2 Features
- **3 PACKAGE DIMENSIONS**
- **4 PUBLICATION ORDERING INFORMATION**
- **5 Documents / Resources** 
  - **5.1 References**
- **6 Related Posts**



onsemi MC74VHC1G08 Single 2 Input And Gate



Single 2-Input AND Gate MC74VHC1G08, MC74VHC1GT08

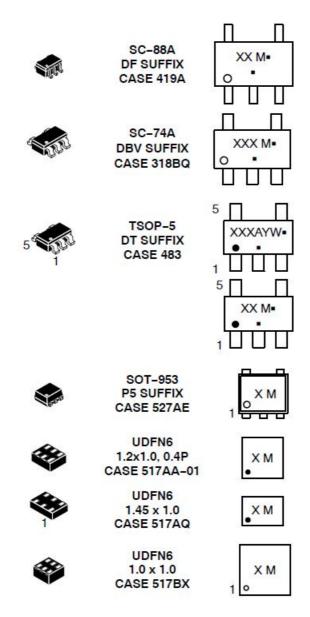
The MC74VHC1G08 / MC74VHC1GT08 is a single 2 input AND gate in tiny footprint packages. The MC74VHC1G08 has CMOS-level input thresholds while the MC74VHC1GT08 has TTL-level input thresholds. The input structures provide protection when voltages up to 5.5 V are applied, regardless of the supply voltage. This allows the device to be used to interface 5 V circuits to 3 V circuits. Some output structures also provide protection when VCC = 0 V and when the output voltage exceeds VCC. These input and output structures help prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

#### **Features**

- Designed for 2.0 V to 5.5 V VCC Operation
- 3.5 ns tPD at 5 V (typ)
- Inputs/Outputs Over-Voltage Tolerant up to 5.5 V
- IOFF Supports Partial Power Down Protection
- Source/Sink 8 mA at 3.0 V
- Available in SC-88A, SC-74A, TSOP-5, SOT-953 and UDFN6 Packages
- Chip Complexity < 100 FETs</li>
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements;
   AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant



Figure 1. Logic Symbol



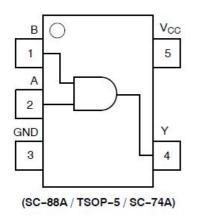
- XX = Specific Device Code
- M = Date Code\*
- A = Assembly Location
- Y = Year
- W = Work Week
- = Pb-Free Package

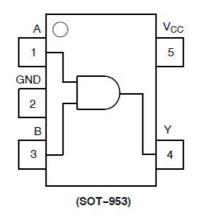
(Note: Microdot may be in either location) \*Date Code orientation and/or position may vary depending upon manufacturing location.

#### **ORDERING INFORMATION**

• See detailed ordering, marking and shipping information on page 8 of this data sheet.

# MC74VHC1G08, MC74VHC1GT08





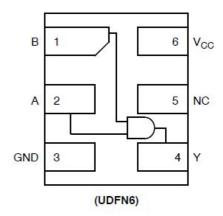


Figure 2. Pinout (Top View)

# PIN ASSIGNMENT (SC-88A / TSOP-5 / SC-74A)

Pin	Function
1	В
2	A
3	GND
4	Y
5	VCC

# PIN ASSIGNMENT (SOT-953)

Pin	Function
1	А
2	GND
3	В
4	Y
5	VCC

# **PIN ASSIGNMENT (UDFN)**

Pin	Function
1	В
2	А
3	GND
4	Y
5	NC
6	VCC

# **FUNCTION TABLE**

Input	Output	
Α	В	Y
L	L	L
L	Н	L
Н	L	L
Н	Н	Н

# MC74VHC1G08, MC74VHC1GT08

# MAXIMUM RATINGS

Symb	Characteristics		Value	Unit
	DC Supply Volta	TSOP-5, SC-88A (NLV) SC-74A, SC-88A, UDFN6, S	-0.5 to +7.0	
VCC	ge	OT-553, SOT-953	-0.5 to +6.5	V

				I	1
VIN	DC Input Voltage	TSOP-5, SC-88A (NLV) So OT-553, SOT-953	C-74A, SC-88A, UDFN6, S	-0.5 to +7.0 -0.5 to +6.5	V
			1Gxx and MC74VHC1GT08P5T5G-L 22088	-0.5 to VCC + 0.	
	DC Output Voltage	(NLV)	1GTxx Active–Mode (Hi gh or Low State)	-0.5 to VCC + 0.	V
			Tri-State Mode (Note 1) Po	-0.5 to +7.0	
VOUT		wer–Down Mode (VCC = 0 V)	-0.5 to +7.0		
		-0.5 to VCC + 0.			
	DC Output Volta ge	Active–Mode (High or Low 1) Power–Down Mode (VC)	-0.5 to +6.5	V	
	Ü	,	-0.5 to +6.5		
IIK	DC Input Diode Current	VIN < GND	-20	mA	
IOK	DC Output Diode (	Current (NLV)	1Gxx and MC74VHC1GT08P5T5G-L 22088 VOUT > VCC, VOUT < GN D	±20	mA
			1GTxx VOUT < GND	-20	
	DC Output Diode Current	VOUT < GND		-20	mA
IOUT	DC Output Source	/Sink Current		±25	mA
ICC or IGND	DC Supply Curren	r Supply Pin or Ground Pin ±50		mA	
TSTG	Storage Temperatu	ure Range		-65 to +150	°C
TL	Lead Temperature	, 1 mm from Case for 10 sec	es	260	°C
TJ	Junction Temperat	ure Under Bias		+150	°C

8JA	Thermal Resista nce (Note 2)	SC-88A SC-74A SOT-553 SOT-953 UDFN6	377 320 324 254 154	° C/ W
PD	Power Dissipatio n in Still Air	SC-88A SC-74A SOT-553 SOT-953 UDFN6	332 390 386 491 812	mW
MSL	Moisture Sensitivit	у	Level 1	-
FR	Flammability Rati	Oxygen Index: 28 to 34	UL 94 V-0 @ 0. 125 in	_
VESD	ESD Withstand Vo	2000	V	
ILatch up	Latchup Performa	nce (Note 4)	±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Applicable to devices with outputs that may be tri-stated.
- 2. Measured with minimum pad spacing on an FR4 board, using 10mm-by-1inch, 2 ounce copper trace no air flow per JESD51-7.
- 3. HBM tested to ANSI/ESDA/JEDEC JS-001-2017. CDM tested to EIA/JESD22-C101-F. JEDEC recommends that ESD qualification to EIA/JESD22-A115-A (Machine Model) be discontinued per JEDEC/JEP172A.
- 4. Tested to EIA/JESD78 Class II.

## **RECOMMENDED OPERATING CONDITIONS**

Symbol	Characteristics	Min	Max	Unit	
VCC	Positive DC Supply Voltage		2.0	5.5	V
VIN	DC Input Voltage	0	5.5	V	
		1Gxx and MC74VHC1GT08P5T5G–L22088	0	VCC	
VOUT	DC Output Voltage (NLV)	1GTxx Active–Mode (High or Lo w State)  Tri–State Mode (Note 1) Power–Do wn Mode (VCC = 0 V)	0 0 0	VCC 5.5 5.5	V
	DC Output Voltage h or Low State) Tri-State Mc C = 0 V)	0 0 0	VCC 5.5 5.5	V	
ТА	Operating Temperature Ran	nge	<b>-</b> 55	+125	°C
	Input Rise and Fall Time SC-88A (NLV) VCC = 3.0 V	0	100		
tr , tf	Input Rise and Fall Time -553, SOT-953 VCC = 2.0 V VCC = 2.3 V to 5 V to 5.5 V	0 0 0 0	20 20 10 5	ns/V	

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS (MC74VHC1G08)

Symb		Test Conditi	VC	TA = 25°C			-40°C £ TA £ 85 °C		-55°C £ TA £ 12 5°C		
Symb	Parameter	ons	) )	Min	Тур	Max	Min	Мах	Min	Мах	Uni t

			2.0	1.5	_	_	1.5	_	1.5	_	
			3.0	2.1	_	-	2.1	_	2.1	_	
VIH	High-Level Input Voltage		4.5	3.1 5	_	_	3.15	_	3.15	_	V
			5.5	3.8 5	_	_	3.85	-	3.85	-	
			2.0	_	_	0.5	_	0.5	_	0.5	
	Low-Level Inpu		3.0	_	_	0.9	_	0.9	_	0.9	
VIL	t Voltage		4.5	-	-	1.35	_	1.35	_	1.35	V
			5.5	_	_	1.65	_	1.65	_	1.65	
VOH	High-Level Out put Voltage	VIN = VIH or VIL IOH = -5 0 μA IOH = - 50 μA IOH = -50 μA IOH = -4 mA IO H = -8 mA	2.0 3.0 4.5 3.0 4.5	1.9 2.9 4.4 2.5 8 3.9 4	2.0 3.0 4.5 -	- - -	1.9 2.9 4.4 2.48 3.80	- - - -	1.9 2.9 4.4 2.34 3.66	- - - -	V
VOL	Low-Level Output Voltage	VIN = VIH or VIL IOL = 50  µA  IOL = 50 µA I OL = 50 µA I OL = 4 mA I OL = 8 mA	2.0 3.0 4.5 3.0 4.5	- - -	0.0 0.0 0.0 - -	0.1 0.1 0.1 0.36 0.36	- - - -	0.1 0.1 0.1 0.44 0.44	- - - -	0.1 0.1 0.1 0.52 0.52	V
IIN	Input Leakage Current	VIN = 5.5 V or GND	2.0 t o 5.	_	_	±0.1	_	±1.0	_	±1.0	μΑ
	Power Off Leak age Current (NL V)	VIN = 5.5 V	0.0	_	_	1.0	_	10	_	10	μΑ

	Power Off Leak age Current	VIN = 5.5 V or VOUT = 5 .5 V	0.0	_	_	1.0	-	10	_	10	μА
ICC	Quiescent Supp ly Current	VIN = VCC o r GND	5.5	_	_	1.0	-	20	_	40	μΑ

Symb		Test Conditi	VC C (V	TA = 25°C			-40°C € TA € 85 °C		-55°C £ TA £ 12 5°C		Uni
ol	Parameter	ons	)	Min	Тур	Max	Min	Max	Min	Max	t
			2.0	1.0	_	_	1.0	-	1.0	_	
VIH F	High-Level		3.0	1.4	_	-	1.4	-	1.4	_	V
VIII	Input Voltage		4.5	2.0	_	-	2.0	-	2.0	_	
			5.5	2.0	_	_	2.0	_	2.0	_	
	Low-Level Inpu t Voltage	-	2.0	_	_	0.28	_	0.28	_	0.28	
VIL			3.0	_	_	0.45	_	0.45	_	0.45	V
VIL			4.5	_	_	0.8	_	0.8	_	0.8	
			5.5	_	_	0.8	_	0.8	_	0.8	
VOH	High-Level Out put Voltage	VIN = VIH or VIL IOH = -5 0 μA IOH = - 50 μA IOH = -50 μA IOH = -4 mA IO H = -8 mA	2.0 3.0 4.5 3.0 4.5	1.9 2.9 4.4 2.5 8 3.9 4	2.0 3.0 4.5 -		1.9 2.9 4.4 2.48 3.80	- - -	1.9 2.9 4.4 2.34 3.66	- - -	V

VOL	Low-Level Output Voltage	VIN = VIH or VIL IOL = 50 $\mu$ A IOL = 50 $\mu$ A I OL = 50 $\mu$ A I OL = 4 mA I OL = 8 mA	2.0 3.0 4.5 3.0 4.5		0.0 0.0 0.0 - -	0.1 0.1 0.1 0.36 0.36	- - -	0.1 0.1 0.1 0.44 0.44	- - -	0.1 0.1 0.1 0.52 0.52	٧
IIN	Input Leakage Current	VIN = 5.5 V or GND	2.0 t o 5. 5	_	_	±0.1	_	±1.0	_	±1.0	μΑ
	Power Off Leak age Current	VIN = 5.5 V or VOUT = 5 .5 V	0	_	_	1.0	_	10	_	10	
Power Off Leak age Current (M C74VHC1GT08 P 5T5G-L22088 Only)	VIN = 5.5 V	0	-	-	1.0	-	10	_	10	μΑ	
ICC	Quiescent Supp ly Current	VIN = VCC o r GND	5.5	_	_	1.0	-	20	_	40	μΑ
ICCT	Increase in Qui es- cent Supply Current per Input Pin	One Input: V IN = 3.4 V; Other Input at VCC or GND	5.5	_	-	1.35	-	1.5	_	1.65	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

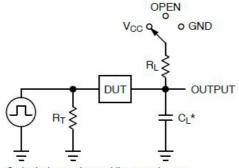
# **AC ELECTRICAL CHARACTERISTICS**

	Parameter Conns			TA = 25°C		-40°C £ TA £ 85 °C		–55°C £ TA £ 12 5°C		Uni	
Symb		Conditio ns	VCC (V)	Min	Тур	Ma x	Min	Max	Min	Max	t
	Propagation Del ay,	CL = 15 p F	3.0 to 3.	_	4.1	8.8	_	10.5	_	12.5	
1		CL = 50 p	6	_	5.9	12. 3	_	14.0	_	16.5	ns
tPHL (Figures 3 4)	(Figures 3 and 4)	CL = 15 p	4.5 to 5.	_	3.5	5.9	_	7.0	_	9.0	
		CL = 50 p		_	4.2	7.9	_	9.0	_	11.0	
CIN	Input Capacitan ce			_	4.0	10	_	10	_	10	pF
COUT	Output Capacitance	Output in High Imp edance S tate		_	6.0	_	_	_	-	-	pF

Symb	Parameter	Typical @ 25°C, VCC = 5 .0 V	Uni t
CPD	Power Dissipation Capacitance (Note 5)	8.0	рF

- CPD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.
- Average operating current can be obtained by the equation: ICC(OPR) = CPD VCC fin + ICC. CPD is used to determine the no-load dynamic power consumption; PD = CPD VCC 2 fin + ICC VCC.

# MC74VHC1G08, MC74VHC1GT08



_		_
C <sub>L</sub> include	les probe ar	nd jig capacitance
R <sub>T</sub> is Z <sub>OI</sub>	JT of pulse of	generator (typically $50 \Omega$ )
f = 1 MH	Z	

Test	Switch Position	C <sub>L</sub> , pF	R <sub>L</sub> , Ω
t <sub>PLH</sub> / t <sub>PHL</sub>	Open	See AC Characteristics Table	Х
t <sub>PLZ</sub> / t <sub>PZL</sub>	V <sub>CC</sub>	ĺ	1 k
t <sub>PHZ</sub> / t <sub>PZH</sub>	GND		1 k

X = Don't Care



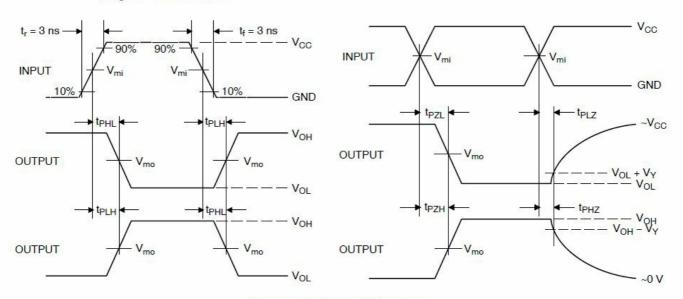


Figure 4. Switching Waveforms

		Vmo, V		
VCC, V	Vmi, V	tPLH, tPHL	tPZL, tPLZ, tPZH, t PHZ	VY, V
3.0 to 3.6	VCC/2	VCC/2	VCC/2	0.3
4.5 to 5.5	VCC/2	VCC/2	VCC/2	0.3

# **ORDERING INFORMATION**

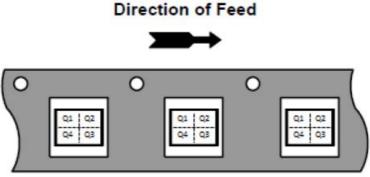
Device	Packages	Specific Device Code	Pin 1 Orientatio n (See below)	Shipping†
MC74VHC1G08DFT1G	SC-88A	V2	Q2	3000 / Tape & Re el
MC74VHC1G08DFT1G-L220 38**	SC-88A	V2	Q2	3000 / Tape & Re el

MC74VHC1G08DFT2G	SC-88A	V2	Q4	3000 / Tape & Re el
MC74VHC1G08DFT2G-F220 38**	SC-88A	V2	Q4	3000 / Tape & Re el
NLVVHC1G08DFT1G*	SC-88A	V2	Q2	3000 / Tape & Re el
NLVVHC1G08DFT2G*	SC-88A	V2	Q4	3000 / Tape & Re el
M74VHC1GT08DFT1G	SC-88A	VT	Q2	3000 / Tape & Re el
M74VHC1GT08DFT1G-L220 38**	SC-88A	VT	Q2	3000 / Tape & Re el
M74VHC1GT08DFT2G	SC-88A	VT	Q4	3000 / Tape & Re el
M74VHC1GT08DFT2G-F220 38**	SC-88A	VT	Q4	3000 / Tape & Re el
NLVVHC1GT08DFT1G*	SC-88A	VT	Q2	3000 / Tape & Re el
NLVVHC1GT08DFT2G*	SC-88A	VT	Q4	3000 / Tape & Re el
MC74VHC1G08DBVT1G	SC-74A	V2	Q4	3000 / Tape & Re el
MC74VHC1GT08DBVT1G	SC-74A	VT	Q4	3000 / Tape & Re el
MC74VHC1G08DTT1G**	TSOP-5	V2	Q4	3000 / Tape & Re el
M74VHC1GT08DTT1G**	TSOP-5	VT	Q4	3000 / Tape & Re el
NLV74VHC1G08DTT1G*	TSOP-5	V2	Q4	3000 / Tape & Re el
NLVVHC1GT08DTT1G*	TSOP-5	VT	Q4	3000 / Tape & Re el
MC74VHC1G08P5T5G	SOT-953	Е	Q2	8000 / Tape & Re el
MC74VHC1G08P5T5G-L220 88**	SOT-953	Е	Q2	8000 / Tape & Re el
MC74VHC1GT08P5T5G	SOT-953	Р	Q2	8000 / Tape & Re el
MC74VHC1GT08P5T5G-L22 088**	SOT-953	P	Q2	8000 / Tape & Re el
MC74VHC1G08MU1TCG	UDFN6, 1.45 x 1.0, 0 .5P	K (Rotated 180° CW)	Q4	3000 / Tape & Re el

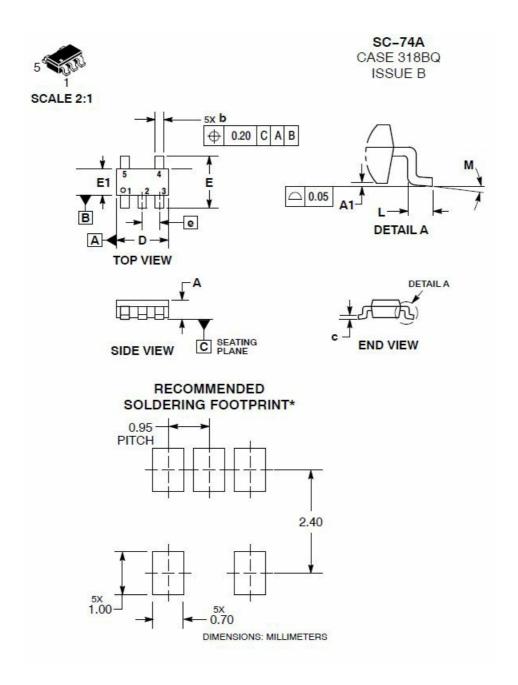
MC74VHC1GT08MU1TCG	UDFN6, 1.45 x 1.0, 0 .5P	4 (Rotated 270° CW)	Q4	3000 / Tape & Re el
MC74VHC1G08MU2TCG	UDFN6, 1.2 x 1.0, 0. 4P	2	Q4	3000 / Tape & Re el
MC74VHC1G08MU3TCG	UDFN6, 1.0 x 1.0, 0. 35	D (Rotated 270° CW)	Q4	3000 / Tape & Re el
MC74VHC1GT08MU3TCG	UDFN6, 1.0 x 1.0, 0. 35	К	Q4	3000 / Tape & Re el

- For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements;
   AEC-Q100 Qualified and PPAP Capable.
- Please refer to NLV specifications for this device.

# PIN 1 ORIENTATION IN TAPE AND REEL



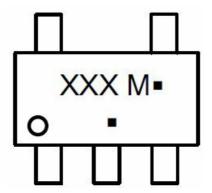
**PACKAGE DIMENSIONS** 



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- 4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE.

	MILLIMETERS			
DIM	MIN	MAX		
Α	0.90	1.10		
A1	0.01	0.10		
b	0.25	0.50		
С	0.10	0.26		
D	2.85	3.15		
Е	2.50	3.00		
E1	1.35	1.65		
е	0.95 BSC			
L	0.20°	0.6°0		
М	0	10		



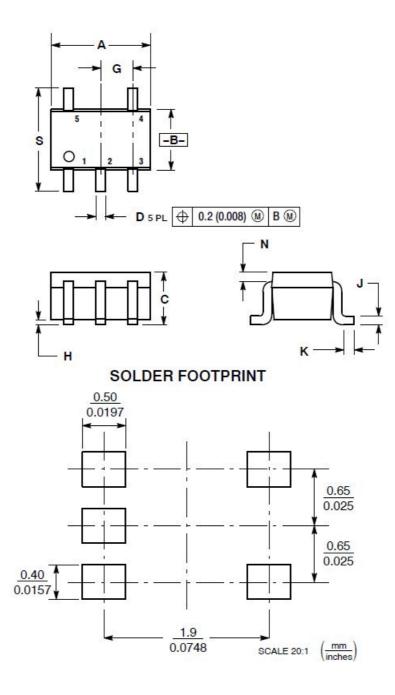
- XXX = Specific Device Code
- M = Date Code
- = Pb-Free Package

(Note: Microdot may be in either location)

• This information is generic. Please refer to the device data sheet for actual part marking. Pb–Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

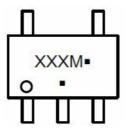
ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries.

ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.



- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.
- 3. 419A-01 OBSOLETE. NEW STANDARD 419A-02.
- 4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.071	0.087	1.80	2.20	
В	0.045	0.053	1.15	1.35	
С	0.031	0.043	0.80	1.10	
D	0.004	0.012	0.10	0.30	
G	0.026 BSC		0.65 BSC		
Н	_	0.004	_	0.10	
J	0.004	0.010	0.10	0.25	
К	0.004	0.012	0.10	0.30	
N	0.008 REF		0.20 REF		
S	0.079	0.087	2.00	2.20	



- XXX = Specific Device Code
- M = Date Code
- = Pb-Free Package

(Note: Microdot may be in either location)

This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

## STYLE 1:

- 1. PIN 1. BASE
- 2. EMITTER
- 3. BASE
- 4. COLLECTOR
- 5. COLLECTOR

# STYLE 2:

- 1. PIN 1. ANODE
- 2. EMITTER
- 3. BASE
- 4. COLLECTOR
- 5. CATHODE

#### STYLE 3:

- 1. PIN 1. ANODE 1
- 2. N/C
- 3. ANODE 2
- 4. CATHODE 2
- 5. CATHODE 1

## STYLE 4:

- 1. PIN 1. SOURCE 1
- 2. DRAIN 1/2
- 3. SOURCE 1
- 4. GATE 1
- 5. GATE 2

## STYLE 5:

Р

- 1. IN 1. CATHODE
- 2. COMMON ANODE
- 3. CATHODE 2
- 4. CATHODE 3
- 5. CATHODE 4

## STYLE 6:

- 1. PIN 1. EMITTER 2
- 2. BASE 2
- 3. EMITTER 1
- 4. COLLECTOR
- 5. COLLECTOR 2/BASE 1

## STYLE 7:

- 1. PIN 1. BASE
- 2. EMITTER
- 3. BASE

- 4. COLLECTOR
- 5. COLLECTOR

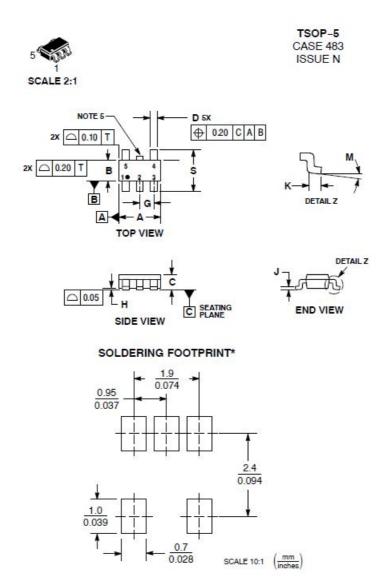
## STYLE 8:

- 1. PIN 1. CATHODE
- 2. COLLECTOR
- 3. N/C
- 4. BASE
- 5. EMITTER

# STYLE 9:

- 1. PIN 1. ANODE
- 2. CATHODE
- 3. ANODE
- 4. ANODE
- 5. ANODE

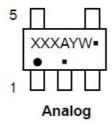
**Note:** Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

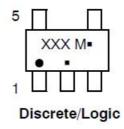


For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- 4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSION A.
- 5. OPTIONAL CONSTRUCTION: AN ADDITIONAL TRIMMED LEAD IS ALLOWED IN THIS LOCATION. TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2 FROM BODY.

	MILLIMETERS				
DIM	MIN	MAX			
Α	2.85	3.15			
В	1.35	1.65			
С	0.90	1.10			
D	0.25	0.50			
G	0.95 BSC				
Н	0.01	0.10			
J	0.10	0.26			
К	0.20°	0.6°0			
М	0	10			
S	2.50	3.00			

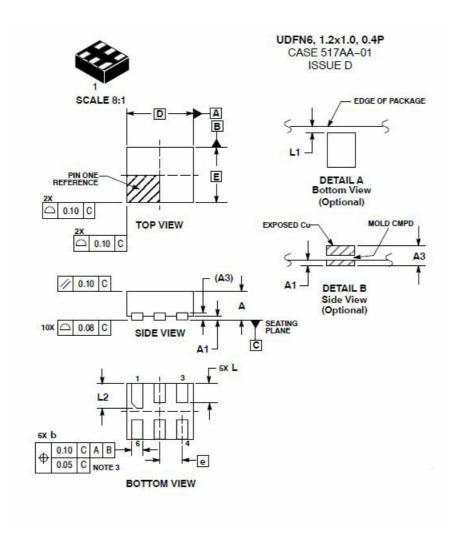




- XXX = Specific Device Code
- A = Assembly Location
- Y = Year
- W = Work Week
- = Pb-Free Package
- XXX = Specific Device Code
- M = Date Code
- = Pb-Free Package

(Note: Microdot may be in either location)

This information is generic. Please refer todevice data sheet for actual part marking.Pb–Free indicator, "G" or microdot "——", may or may not be present.



- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
- 3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.25 AND 0.30 mm FROM TERMINAL.
- 4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

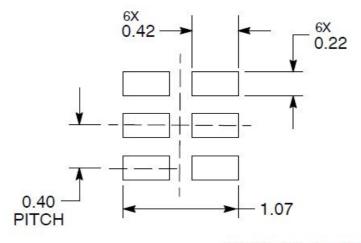
	MILLIMETERS		
DIM	MIN	MAX	
Α	0.45	0.55	
A1	0.00 0.05		
A3	0.127 REF		
b	0.15	0.25	
D	1.20 BSC		
Е	1.00 BSC		
е	0.40 BSC		
L	0.30	0.40	
L1	0.00	0.15	
L2	0.40	0.50	



- X = Specific Device Code
- M = Date Code

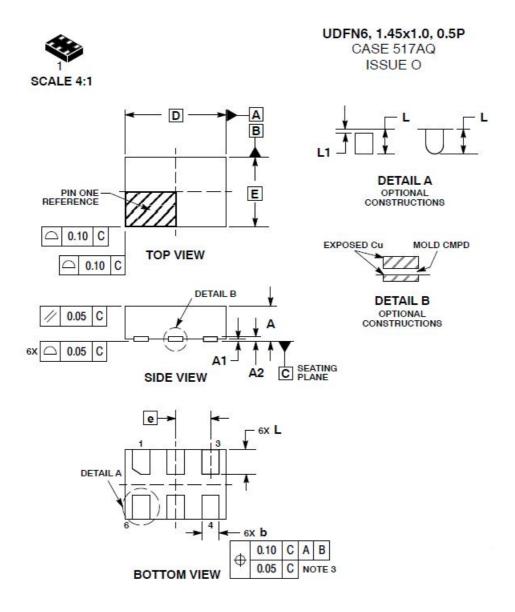
\*This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot "——", may or may not be present.

# **MOUNTING FOOTPRINT**



**DIMENSIONS: MILLIMETERS** 

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.





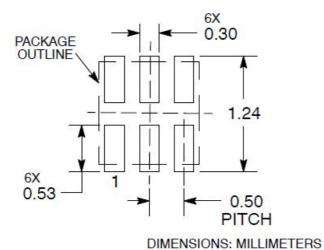
- X = Specific Device Code
- M = Date Code

This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot "——", may or may not be present.

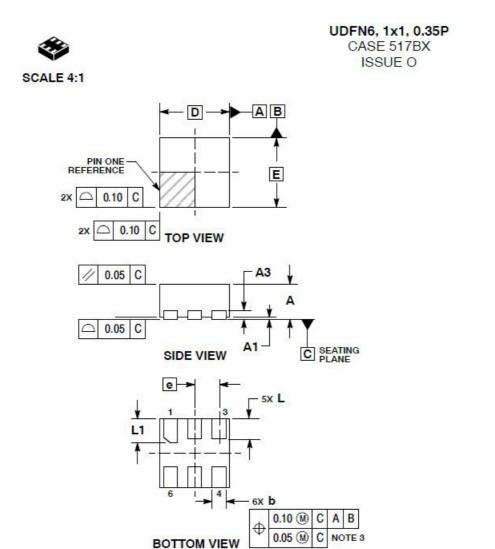
- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
- 3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 mm FROM THE TERMINAL TIP.

	MILLIMETERS			
DIM	MIN	MAX		
Α	0.45 0.55			
A1	0.00	0.05		
A2	0.07 REF			
b	0.20	0.30		
D	1.45 BSC			
Е	1.00 BSC			
е	0.50 BSC			
L	0.30	0.40		
L1		0.15		

# **MOUNTING FOOTPRINT**



For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.





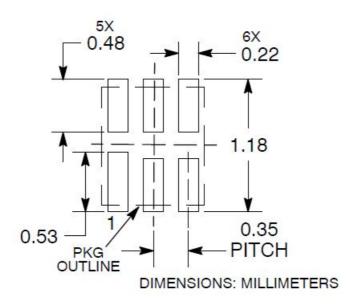
- X = Specific Device Code
- M = Date Code

This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot —, may or may not be present. Some products may not follow the Generic Marking.

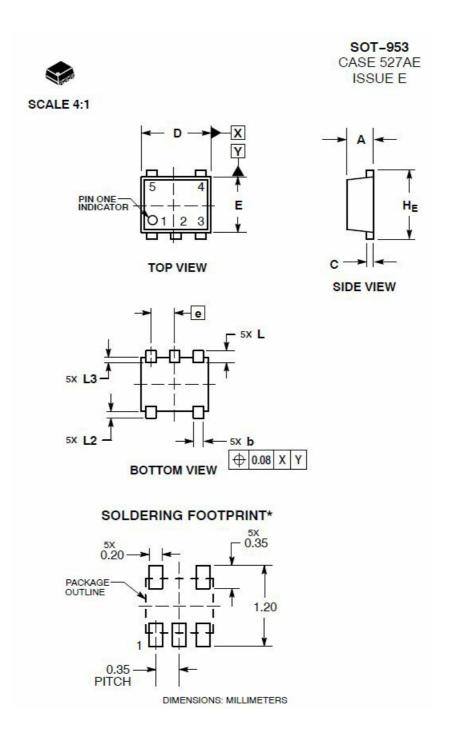
- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
- 3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20 MM FROM TERMINAL TIP.
- 4. PACKAGE DIMENSIONS EXCLUSIVE OF BURRS AND MOLD FLASH.

	MILLIMETERS		
DIM	MIN	MAX	
Α	0.45 0.55		
<b>A1</b>	0.00	0.05	
<b>A3</b>	0.13 REF		
b	0.12	0.22	
D	1.00 BSC		
Ε	1.00 BSC		
е	0.35 BSC		
L	0.25	0.35	
L1	0.30	0.40	

# RECOMMENDED SOLDERING FOOTPRINT\*



For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			
DIM	MIN	NOM	MAX	
Α	0.34	0.37	0.40	
b	0.10	0.15	0.20	
С	0.07	0.12	0.17	
D	0.95	1.00	1.05	
E	0.75	0.80	0.85	
е	0.35 BSC			
HE	0.95	1.00	1.05	
L	0.175 REF			
L2	0.05	0.10	0.15	
L3			0.15	



- X = Specific Device Code
- M = Month Code

This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot "—", may or may not be present.

onsemi, , and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <a href="https://www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising

out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts, onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use onsemi products for any such unintended or unauthorized application, Buyer shall indemnify and hold onsemi and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that onsemi was negligent regarding the design or manufacture of the part, onsemi is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

#### **PUBLICATION ORDERING INFORMATION**

• LITERATURE FULFILLMENT:

• Email Requests to: orderlit@onsemi.com

• onsemi Website: www.onsemi.com

#### **TECHNICAL SUPPORT**

• North American Technical Support:

Voice Mail: 1 800–282–9855 Toll Free USA/Canada

• Phone: 011 421 33 790 2910

#### **Europe, Middle East and Africa Technical Support:**

• Phone: 00421 33 790 2910

• For additional information, please contact your local Sales Representative

#### **Documents / Resources**



onsemi MC74VHC1G08 Single 2 Input And Gate [pdf] User Guide MC74VHC1G08 Single 2 Input And Gate, MC74VHC1G08, Single 2 Input And Gate, 2 Input And Gate, Gate

#### References

- OIntelligent Power and Sensing Technologies | onsemi
- User Manual

Manuals+,